

oxidizing, in response to said applying, at least a portion of the metal layer to form a metal oxide to function as a dielectric layer.

50. (Amended) The method of claim 38, wherein the metal layer includes titanium [and conductive layer includes polysilicon].

51. (Amended) The method as specified in Claim 50, further comprising:
forming the [first] metal layer from at least one of titanium, copper, gold, tungsten and nickel.

76. (Amended) A method of forming a capacitor, comprising:
forming [an electrically isolated] a polysilicon layer overlying a substrate, the polysilicon layer having portions electrically isolated from one another;
forming a conformal metal layer atop the polysilicon layer portions;
electrolytically oxidizing at least a portion of the conformal metal layer; and
covering the oxidized portion of the metal layer with a conductive layer.

REMARKS

Applicant has carefully reviewed and considered the Office Action mailed on June 18, 2002, and the references cited therewith.

Claims 37, 50, 51, and 76 are amended. As a result, claims 2-6, 10-18, 29-38, 50-52, 76 and 77 remain pending in this application.

35 USC §112 Rejection of the Claims

Claims 51 and 52

Claims 51 and 52 were rejected under 35 USC § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which Applicant regards as the invention.